

Historical Notes on Solid-State Microwave Heating

Eli Schwartz

Microwave-Energy Laboratory, Faculty of Engineering, Tel Aviv University
 E-mail: mail2eli.s@gmail.com

The use of solid-state microwave generators for heating was already proposed in the late sixties of the previous century. In 1971, McAvoy was granted the first patent on the “solid state microwave oven”¹. This invention was followed in the seventies by several other patents related to the various aspects of solid-state microwave heating. In 1972, Cheng patented the “solid state microwave heating apparatus”², in which the cavity walls also functioned as the heatsink of the solid-state devices radiated by dipole antennas. In 1975, Ohtani patented the “hybrid microwave heating apparatus”³, combining the conventional magnetron as a high-power source with auxiliary solid-state devices in order to attain better heating uniformity.

In 1977, Dehn patented the “microwave heating apparatus with improved multiple couplers and solid-state power source”⁴. This patent presented a cut-off of tubular housing for mounting multiple solid-state oscillators using micro-strip circuitry. The couplers were longitudinally spaced and angularly staggered so that the energy was coupled to different regions. In 1976, Bickel patented the “solid-state microwave oven power source”⁵, which incorporated plurality of high-power oscillators.

In 1980, Mackay granted two patents referring to “controlled heating microwave ovens using different operating frequencies”^{6,7}. These patents presented a frequency agile microwave source for energizing the oven cavity in an optimal spatial pattern. The frequencies at which the oven’s cavity was energized were selected by the control system in order to obtain improved heating uniformity by superimposing various heating patterns. These pioneering inventions, already patented by the year 1980, were followed by additional patents as partially listed in Table 1 and illustrated in Figs. 1 and 2.

The first archived papers on solid-state microwave heating were published in 1979 by Mackay, Tinga and Voss⁸. The main obstacles encountered in these early studies were the relatively high cost, low power and poor efficiency of the solid-state generators available then as compared to magnetrons⁹.

In the early 2000’s, the laterally-diffused metal-oxide semiconductor (LDMOS) technology became mature and cost-effective, in particular for the market segment of cellular communication base-stations. The demands for high-power, low-cost LDMOS transistors for the huge mobile-phone market have also paved the way to embed LDMOS transistors into microwave-heating applications, with the expectation to be almost competitive with the pricing of conventional magnetron systems.

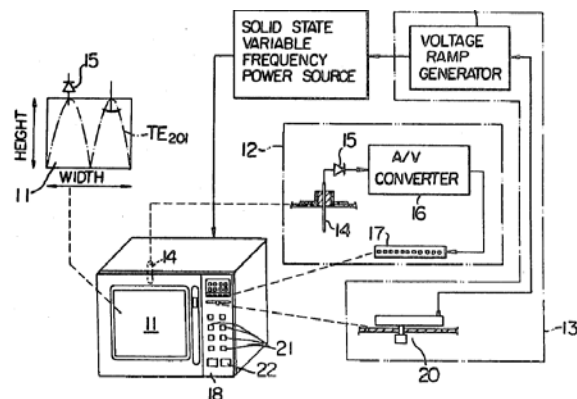


Figure 1. A frequency control scheme for solid-state microwave ovens [Nobue, US pat. 4415789, 1983].

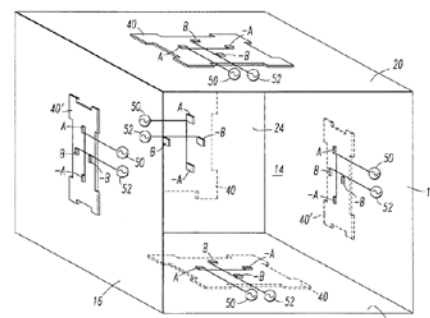


Figure 2. Distributed microwave radiators for heating applications [Page, US pat. 5558800, 1996].

Table 1. A partial list of patents on solid-state microwave heating since 1971

| Year | Title | Inventor | Patent No |
|------|---|-------------------|----------------|
| 1971 | Solid-state microwave oven | Bruce R. McAvoy | US 3557333 |
| 1972 | Solid-state microwave heating apparatus | Kern K. Cheng | US 3691338 |
| 1975 | Hybrid microwave heating apparatus | Tetsuro Ohtani | US 3867607 |
| 1977 | Microwave heating apparatus with improved multiple couplers and solid-state power source | Rudolph A. Dehn | US 4006338 |
| 1978 | Solid-state microwave oven power source | Samuel H. Bickel | US 4097708 |
| 1980 | Controlled heating microwave ovens | Alejandro MacKay | US 4196332 |
| 1980 | Controlled heating microwave ovens using different operating frequencies | Alejandro MacKay | CA 1081796 |
| 1983 | Microwave oven having controllable frequency microwave power source [Figure 1] | Tomotaka Nobue | US 4415789 |
| 1985 | Microwave heating apparatus with solid-state microwave oscillating device | Hisashi Okatsuka | US 4504718 |
| 1995 | Microwave oven, in particular for rapid heating to high temperature | Patrick Jackuault | US 5420401 |
| 1995 | Solid-state microwave generating array material, each element of which is phase controllable, and plasma processing systems | Jerome J. Cuomo | EP 0459177 |
| 1996 | Active RF cavity including a plurality of solid-state transistors | Bernard R. Cheo | US 5497050 |
| 1996 | Microwave power radiator for heating applications [Figure 2] | Derrick J. Page | US 5558800 |
| 2004 | Microwave heating using distributed semiconductor sources | Peter Handinger | US 20040206755 |
| 2010 | Microwave oven switching between predefined modes | Ulf E. Nordh | US 20100155392 |
| 2011 | Microwave heating apparatus [Figure 4] | Tomotaka Nobue | US 20110108548 |
| 2013 | Microwave oven with antenna array | Ranjit Gharpurey | US 20130175262 |
| 2015 | Microwave oven using solid-state amplifiers and antenna array | Jose A. Lima | US 20150136760 |
| 2016 | Versatile microwave heating apparatus | Olle Niklasson | US 9332597 |

A solid-state microwave heater for loads of ~10-cc volume was presented in 2006 at IMPI-40 by Schwartz et al.¹⁰. This laboratory heater, shown in Figs. 3a,b, introduced the first use known to the author of an LDMOS amplifier for microwave heating purposes. The positive feedback scheme employed in this device adapts the oscillation frequency to the load variation in the frequency domain due to the temperature increase, as shown in Fig. 3c. This scheme was found also useful for localized-microwave heating (LMH) induced by solid-state applicators, such as various microwave drills^{11,12} and metallic fuel igniters¹³.

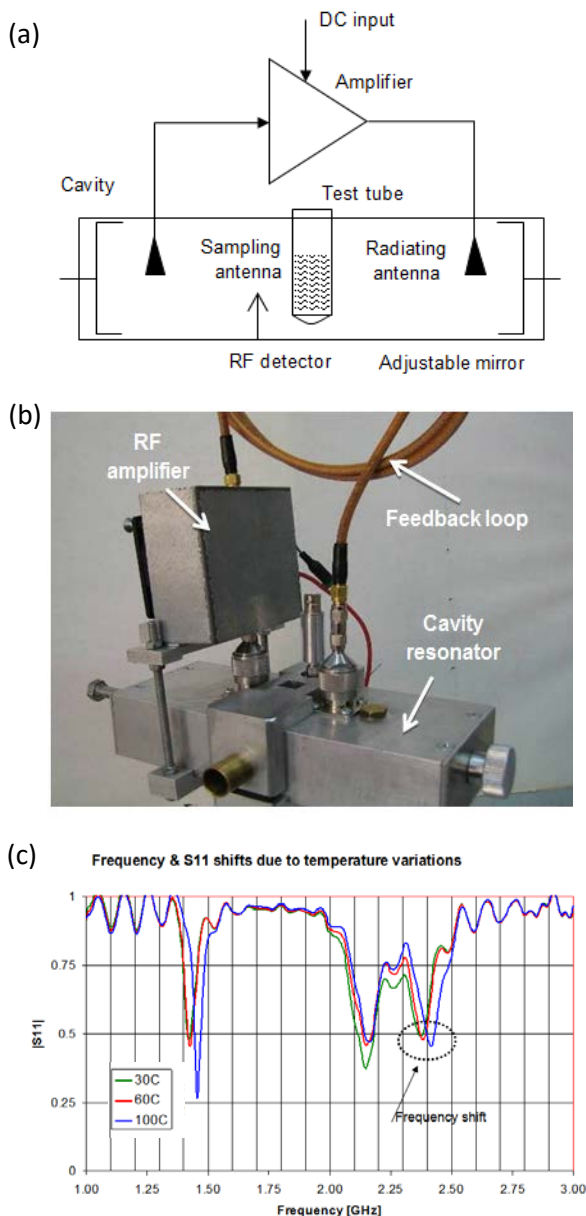


Figure 3. A transistor-based microwave heater¹⁰ [Schwartz et al. 2006]: (a) The positive-feedback scheme, (b) the device, (c) the resonance shift with the temperature.

More recently, techniques for efficiency improvement were investigated by Korpas¹⁴, and by Imiatez¹⁵ for healthcare applications. Advanced techniques, applying algorithms to control the frequency and phase in order to optimize the efficiency, were studied in GaN¹⁶. Multiple source analyses, in order to control the heating pattern, were presented by Yakovelev¹⁷.

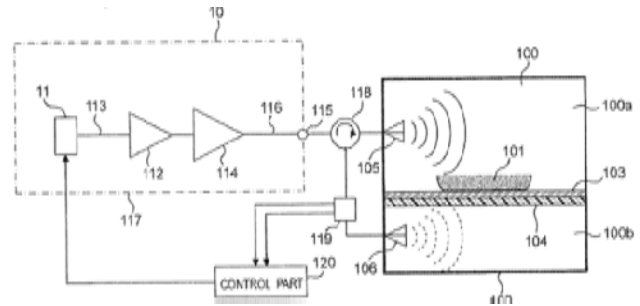


Figure 4. A two-stage microwave oven scheme [Nobue, US pat. US 20110108548, 2011]

Despite the evident technological feasibility of the solid-state technology for microwave heating, as reflected in the literature since the first patent in 1971, the magnetron vacuum tube has dominated this field for over five decades. Only recently, the potential market value of solid-state microwave heating systems, in particular for domestic microwave-ovens, triggered several companies to develop, patent and commercialize this technology. In 2013, RF Dynamics Ltd. (renamed to Goji) reported the development of a solid-state microwave oven and claimed then to achieve a quick, precise and efficient cooking system¹⁸. A commercial demonstrator of a solid-state oven was also announced in 2015 by Freescale/NXP^{19,20}.

Although LDMOS technology is the most commonly used for high power solid-state devices, the noticeable performance advantages of the continually improving and growing GaN technology is being the trigger to pursue for low-cost high-volume manufacturing. Lately, at the IMS-2016 exhibition in San Francisco, several companies presented mature GaN devices; MACOM presented a GaN-on-silicon amplifier for 2.45-GHz CW ISM applications, with 300-W saturated power and manufacturing capabilities for 8" wafers. Other GaN devices from AMPLION, QORVO, INFINEON, NXP, and RFHIC, have also been presented. Heating applicators based on GaN devices, presented mostly for cooking, are yet not available for

consumers and high-volume manufacturing, but they indeed demonstrate the technological capabilities. NXP presented 900-mL battery-operated portable heater based on a 200-W LDMOS device. MACOM and MIDEA also presented a microwave-oven based on a 300-W GaN device, designed to provide homogeneous field pattern inside the cavity.

It appears that the solid-state microwave heating technology is promising and compelling to replace the conventional magnetron tubes sometime in the near future. This trend is justified mainly by the small form factor, the low operating voltage, and the ability to precisely control the phase and frequency in order to obtain better heat distribution.

GaN devices present noticeable advantages over the LDMOS technology especially at 2.45-GHz and higher frequencies, and it seems to be the dominant device for solid-state heating applications in future. Its main advantages are the high breakdown voltage, higher efficiency, and higher gain and power density. Its main obstacle is yet the high price, though it is gradually being reduced. These days, according to MACOM, the GaN price is becoming competitive to the common LDMOS costs.

The goal of having a significant market share for the solid-state heating systems will be achieved by reducing the price gap between the magnetron and the LDMOS/GaN devices. Once this cost target will be achieved, the microwave heating technology will become ubiquity. The heating and cooking with solid-state microwave ovens will be more precise, more controllable, and much more fascinating.

For further reading:

1. B. R. McAvoy, "Solid state microwave oven," US Patent 4097708, Jan 21, 1971.
2. K. K. Cheng, "Solid state microwave heating apparatus," US Patent 3691338, Sep 12, 1972.
3. T. Ohtani, "Hybrid microwave heating apparatus," US Patent 3867607, Feb 18, 1975.
4. R. A. Dehn, "Microwave heating apparatus with improved multiple couplers and solid-state power source," US Patent 4006338, Feb 1, 1977.
5. S. H. Bickel, "Solid state microwave oven power source," US Patent 4097708, Jan 27, 1978.
6. A. B. MacKay, "Controlled heating microwave ovens," US Patent 4196332, Apr 1, 1980.

7. A. B. MacKay, "Controlled heating microwave ovens using different operating frequencies," CA Patent 1081796, Jul 15, 1980.
8. A. B. Mackay, W. R. Tinga, W. A. G. Voss, "Frequency agile sources for microwave ovens," Jour. Microwave Power & Electromagnetic Energy, Vol. 14, pp 63-76, 1979.
9. W. A. G. Voss, "Solid state microwave oven development," Jour. Microwave Power & Electromagnetic Energy, Vol. 21, pp 188-189, 1986.
10. E. Schwartz, A. Anaton, D. Huppert, and E. Jerby, "Transistor-based miniature microwave heater," Proc. IMPI 40th Int'l Microwave Symposium, Boston, Aug, 9-11, 2006, pp. 246-249.
11. O. Mela, E. Jerby, "Miniature transistor-based microwave drill," Proc. Global Congress Microwave Energy Applications (GCMEA-1), Otsu, Japan, 2008, pp. 443-446.
12. Y. Meir, E. Jerby, "Localized rapid heating by low-power solid-state microwave-drill," IEEE-MTT Trans. Microw. The. & Tech., Vol. 60, pp. 2665-2672, 2012.
13. Y. Meir, E. Jerby, "Thermite-powder ignition by electrically-coupled localized microwaves," Combust. Flame, Vol. 159, pp. 2474-2479, 2012.
14. P. Korpas et al, "Application study of new solid-state high-power microwave sources for efficiency improvement of commercial domestic ovens," Proc. IMPI 47 Annual Microwave Power Symposium, Rhode Island, 2013.
15. A. Imtiaz et al., "A high power high efficiency integrated solid-state microwave heating structure for portable diagnostic healthcare applications," Proc. IEEE MTT-S, London UK, pp. 1-3, 2014.
16. P. Korpas, et al. "Effects of applying a frequency and phase-shift efficiency optimization algorithm to a solid-state microwave oven," Proc. 20 Intern. Conf. on Microwaves, Radar, and Wireless Comm., Lviv, Ukraine, pp. 1-4, 2014.
17. V. Yakovlev, "Frequency control over the heating patterns in a solid-state dual-source microwave oven," Int'l Microwave Symposium (IMS), IEEE MTT-S, Phoenix, AZ, 2015.
18. http://cache.nxp.com/files/rf_if/doc/white_paper/VOLUME_TRIC_COOKING_GOJI_TECH.pdf?fsrch=1&sr=2&pageNum=1
19. http://www.designnews.com/document.asp?doc_id=277959
20. <http://www.nxp.com/products/rf/rf-sage:RF-SAGE-PG>

About the Author:



Eli Schwartz received his M.Sc. degree in electrical engineering at Tel Aviv University. He worked on solid-state microwave heaters under the supervision of Prof. Eli Jerby in the years 2005-2006. Mr. Schwartz is currently a senior RFIC engineer at DSP

Group in the R&D division, working on next-generation mobile wireless solutions such as CMOS RF power amplifiers. Prior to that, he held various RFIC positions at Intel, working on millimeter-wave circuits.